

OAI 33 (Static)

Group Number: 14



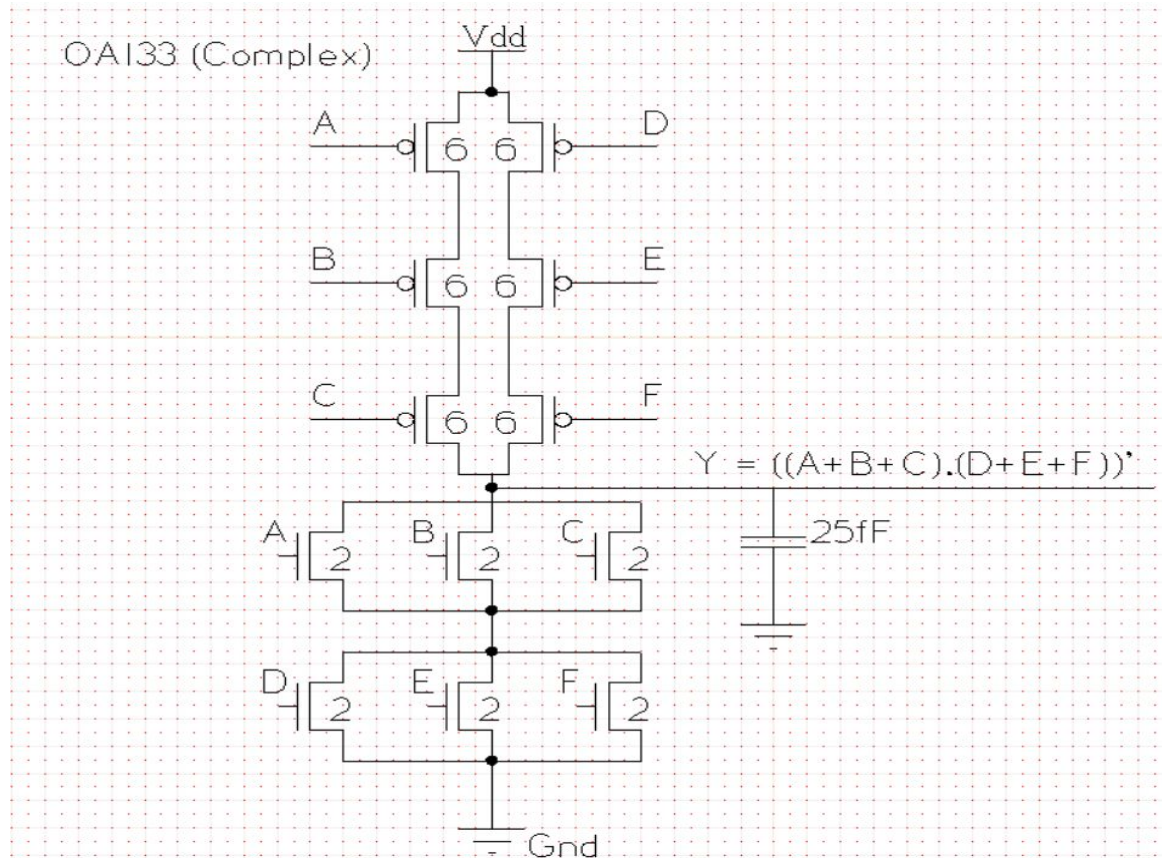
INDRAPRASTHA INSTITUTE *of*
INFORMATION TECHNOLOGY
DELHI

Group Members

- Abhinav Kumar Saxena (2022018)
- Akanksh Semar (2022046)
- Harsh Nangia (2022199)
- Kunal (2022260)

Schematic + Sizing (Complex)

(1/2)

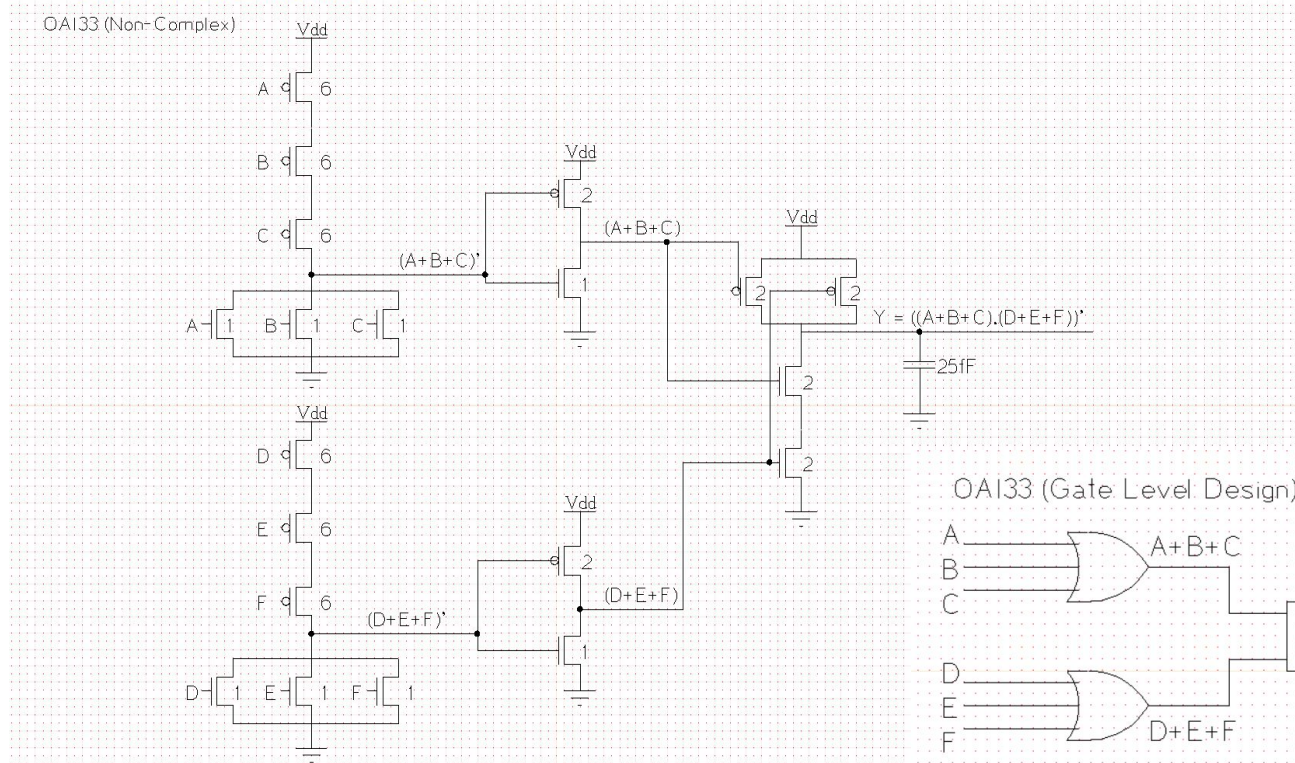


$1u = 0.135\mu m$

Size of PMOS = $0.81\mu m$

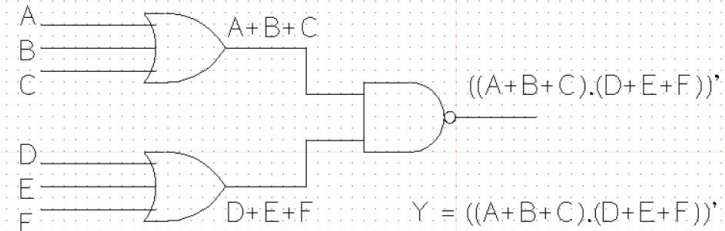
Size of NMOS = $0.27\mu m$

Schematic + Sizing (Non-Complex) (2/2)



$$1u = 0.135\mu m$$

OAI33 (Gate Level Design)



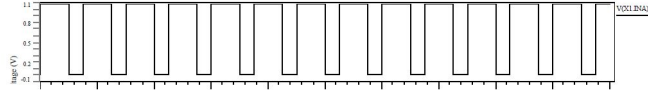
Waveforms for Complex (1/2)

$$Y = ((A+B+C).(D+E+F))'$$

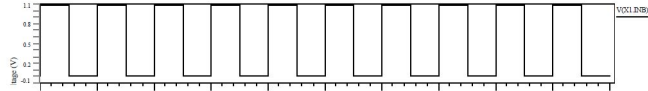


Pre Layout

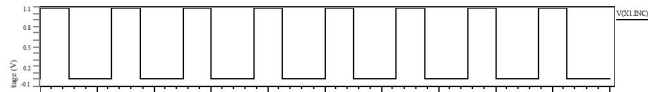
inA



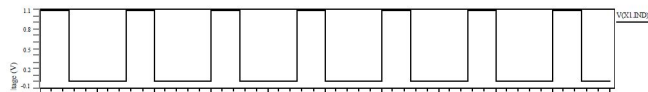
inB



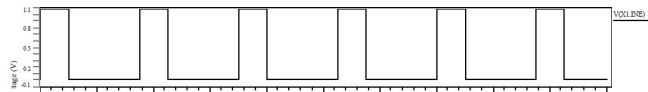
inC



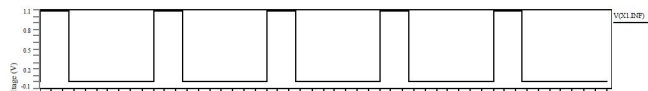
inD



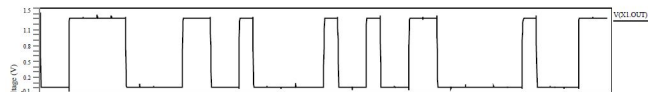
inE



inF

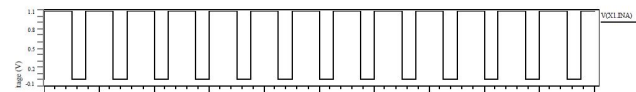


out

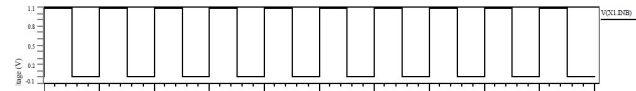


Post Layout

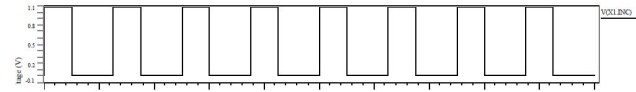
inA



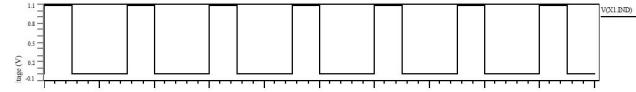
inB



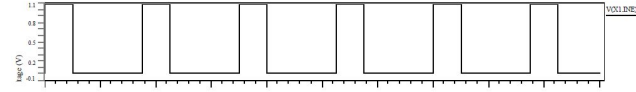
inC



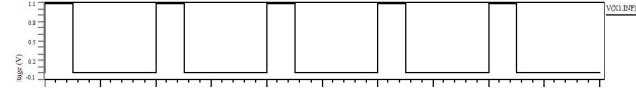
inD



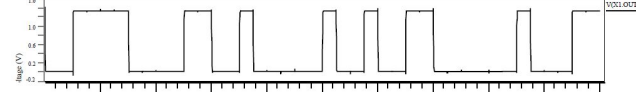
inE



inF



out



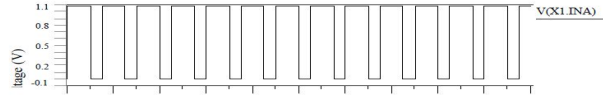
Waveforms for Non-Complex (2/2)

$$Y = ((A+B+C).(D+E+F))'$$

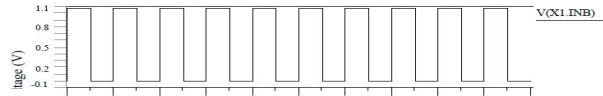


Pre Layout

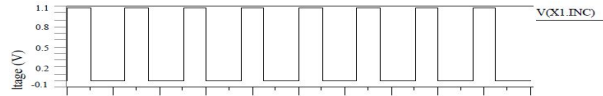
inA



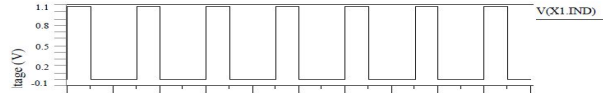
inB



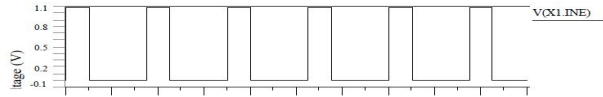
inC



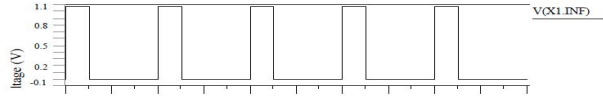
inD



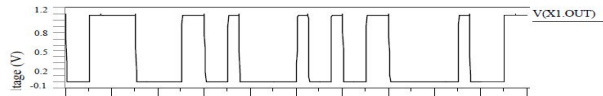
inE



inF

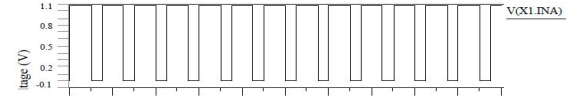


out

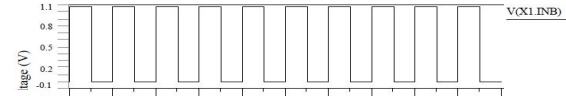


Post Layout

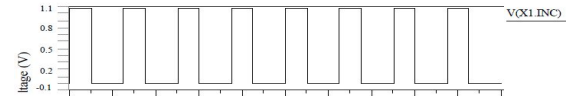
inA



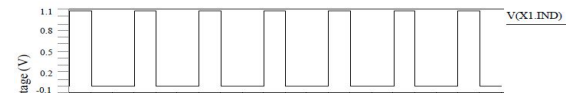
inB



inC



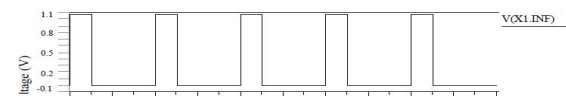
inD



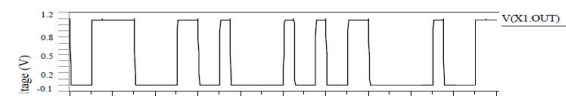
inE



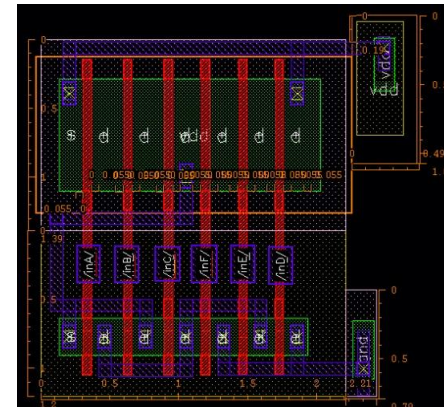
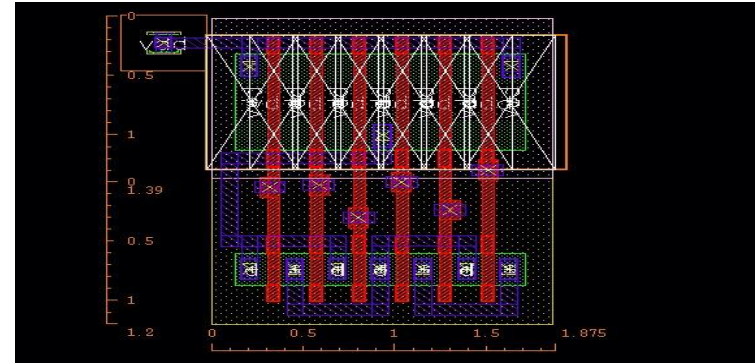
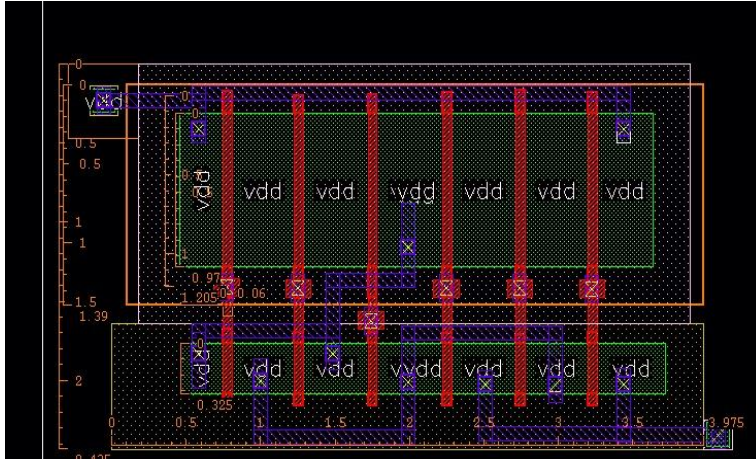
inF



out



Challenges while Designing Layout (1/3)

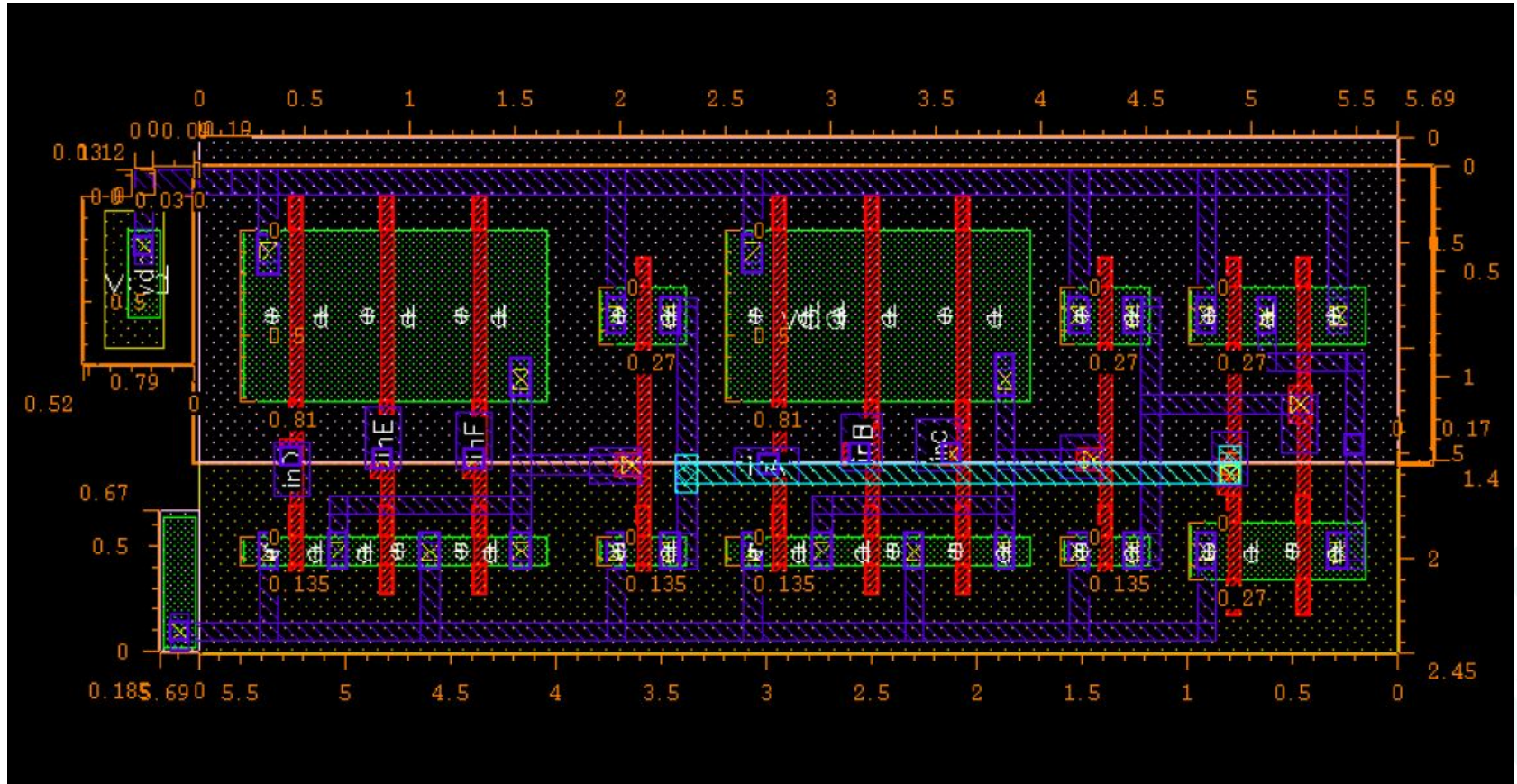


Our Learnings:

1. Each Source and drain should have a different OD layer and one common OD layer for all the PMOS/NMOS if shared together.
2. Making a custom layout helps us reduce Area and get minimum DRC errors.
3. The area occupied by input Vias(M1-PO) should be taken care of while creating the layout to avoid workload in future.
4. Dont use ChatGPT for Layout, it can increase the workload, asking Faculty, TAs and Seniors helps the most when you are stuck.

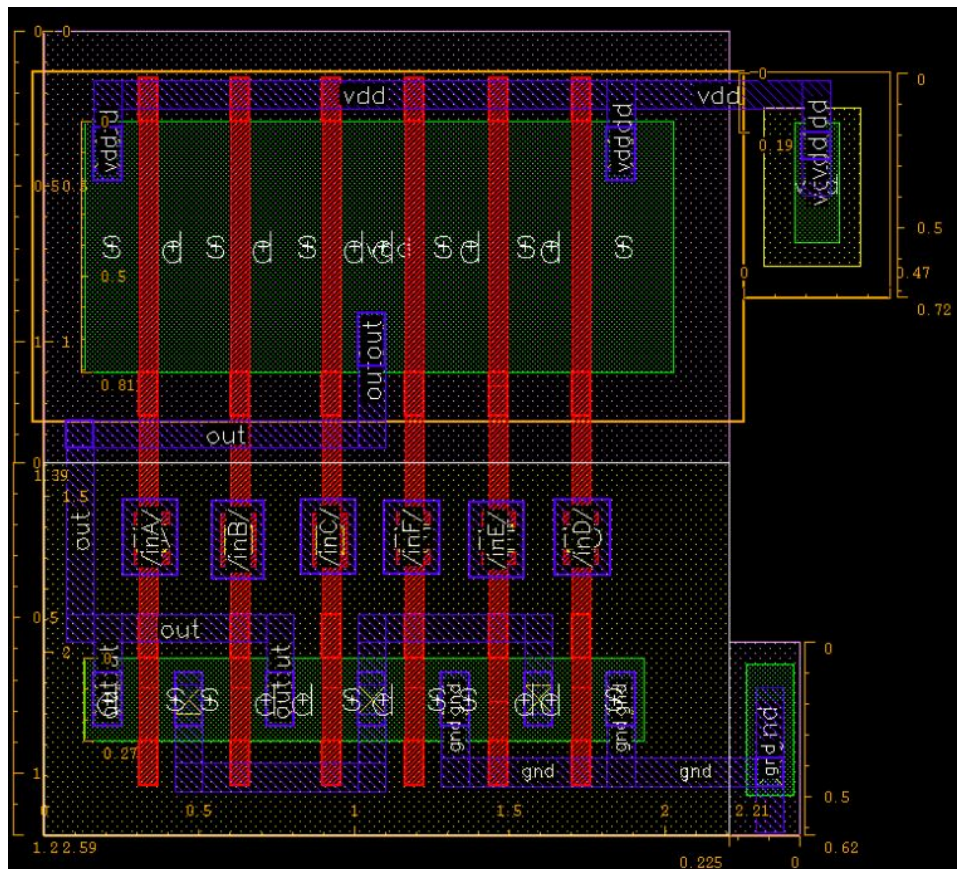
Layout (Non-Complex)

(2/3)



Layout (Complex)

(3/3)



Complex

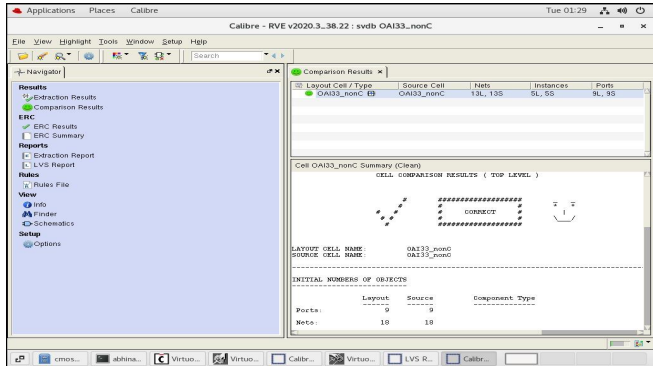
Area = $5.7239 \mu\text{m}^2$ (excluding Vdd & Gnd Vias)
Total Area = $6.2018 \mu\text{m}^2$

Non-Complex

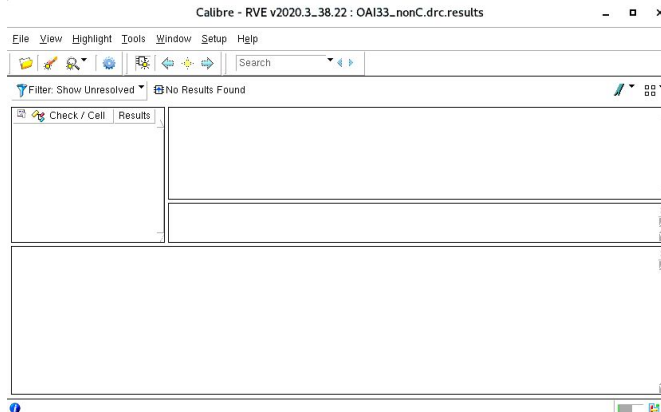
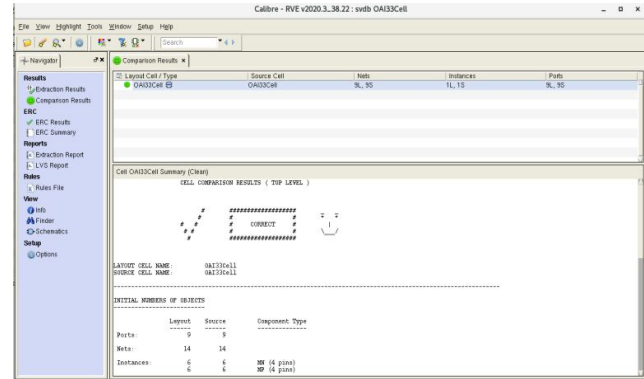
Area = $14.2365 \mu\text{m}^2$ (excluding Vdd & Gnd Vias)
Total Area = $14.77018 \mu\text{m}^2$

	Complex	Non Complex
Number of Transistors	12	20
Area	$6.2018 \mu\text{m}^2$	$14.7712 \mu\text{m}^2$
Height	13 tracks	13 tracks
Width	14 tracks	32 tracks

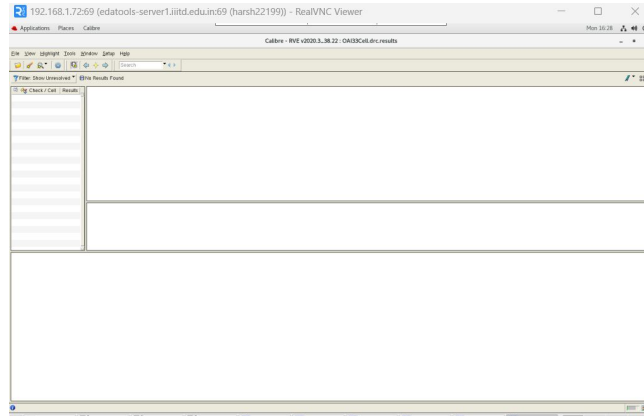
DRC, ERC and LVS Reports



LVS & ERC
Clean



DRC Clean



Non Complex

Complex

Verification Results (for all PVTs) tpd,tcd & power (1/2)



Pre Layout Simulations

PVT	tpd(ns)	tcd(ns)	Power(μW)
FF, 1.32V, -40C	0.049	0.021	1.99
FF, 1.32V, 125C	0.063	0.028	3.18
SS, 1.08V, 125C	0.111	0.051	1.43
SS, 1.08V, -40C	0.086	0.039	1.34

PVT	tpd(ns)	tcd(ns)	Power (μW)
FF, 1.32V, -40C	0.079	0.044	2.28
FF, 1.32V, 125C	0.100	0.056	4.05
SS, 1.08V, 125C	0.213	0.123	1.63
SS, 1.08V, -40C	0.171	0.099	1.53

Complex

Post Layout Simulations

PVT	tpd(ns)	tcd(ns)	Power(μW)
FF, 1.32V, -40C	0.050	0.023	2.02
FF, 1.32V, 125C	0.066	0.029	3.22
SS, 1.08V, 125C	0.116	0.055	1.45
SS, 1.08V, -40C	0.090	0.042	1.37

PVT	tpd(ns)	tcd(ns)	Power(μW)
FF, 1.32V, -40C	0.080	0.044	2.30
FF, 1.32V, 125C	0.101	0.056	4.07
SS, 1.08V, 125C	0.214	0.124	1.65
SS, 1.08V, -40C	0.172	0.100	1.55

Non Complex

Verification Results (for all PVTs) t_{fall} & t_{rise} (2/2)



Pre Layout Simulations

PVT	$t_{fall}(ns)$	$t_{rise}(ns)$
FF, 1.32V, -40C	0.059	0.065
FF, 1.32V, 125C	0.074	0.082
SS, 1.08V, 125C	0.117	0.16
SS, 1.08V, -40C	0.076	0.1399

Complex

Post Layout Simulations

PVT	$t_{fall}(ns)$	$t_{rise}(ns)$
FF, 1.32V, -40C	0.0613	0.067
FF, 1.32V, 125C	0.074	0.085
SS, 1.08V, 125C	0.12	0.17
SS, 1.08V, -40C	0.077	0.14

PVT	$t_{fall}(ns)$	$t_{rise}(ns)$
FF, 1.32V, -40C	0.095	0.061
FF, 1.32V, 125C	0.137	0.073
SS, 1.08V, 125C	0.309	0.120
SS, 1.08V, -40C	0.230	0.106

Non Complex

PVT	$t_{fall}(ns)$	$t_{rise}(ns)$
FF, 1.32V, -40C	0.095	0.062
FF, 1.32V, 125C	0.138	0.074
SS, 1.08V, 125C	0.313	0.123
SS, 1.08V, -40C	0.235	0.106

Analysis



	PVTs
Best Case (TCD)	FF, 1.32V, -40C
Worst Case (TPD)	SS, 1.08V, 125C
Worst Power	FF, 1.32V, 125C

	Complex	Non Complex
Number of Transistors	12	20
Area	6.2018 μm^2	14.7712 μm^2 (2.3x Complex)
Power	Less	More (1.2x for FF,125,1.32)
Delays	Less	More

Present Work Distribution (after mid sem presentation)

Complex Layout - Abhinav Kumar Saxena, Harsh Nangia

Non Complex Layout - Abhinav Kumar Saxena, Akanksh Semar, Harsh Nangia, Kunal

Simulations Complex Post Layout - Abhinav Kumar Saxena, Akanksh Semar, Harsh Nangia, Kunal

Simulations Non Complex Post Layout - Abhinav Kumar Saxena, Harsh Nangia, Kunal

Previous Work Distribution (Midsem Presentation)

Schematics + Sizing for Complex - Cumulative Efforts

Schematics + Sizing for Non Complex - Cumulative Efforts

Stick Diagram for Complex - Abhinav Kumar Saxena, Akanksh Semar, Kunal

Stick Diagram for Non Complex - Kunal, Harsh Nangia, Akanksh Semar

Simulations Complex PreLayout - Abhinav Kumar Saxena, Harsh Nangia, Kunal

Simulations Non Complex PreLayout - Abhinav Kumar Saxena, Akanksh Semar, Harsh Nangia, Kunal